To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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HD74HC540/HD74HC541

Octal Buffers/Line Drivers (with 3-state outputs)

ADE-205-508 (Z)
1st. Edition
Sep. 2000

Description

The HD74HC540 is an inverting buffer and the HD74HC541 is a non-inverting buffer. The 3-state control gate operates as a two-input NOR such that if either $\overline{G}_1$ or $\overline{G}_2$ are high, all eight outputs are in the high-impedance state.

Features

- High Speed Operation: t_{pd} = 11.5 ns typ (C_L = 50 pF)
- High Output Current: Fanout of 15 LSTTL Loads
- Wide Operating Voltage: V_{CC} = 2 to 6 V
- Low Input Current: 1 μA max
- Low Quiescent Supply Current: I_{CC} (static) = 4 μA max (Ta = 25°C)

Function Table

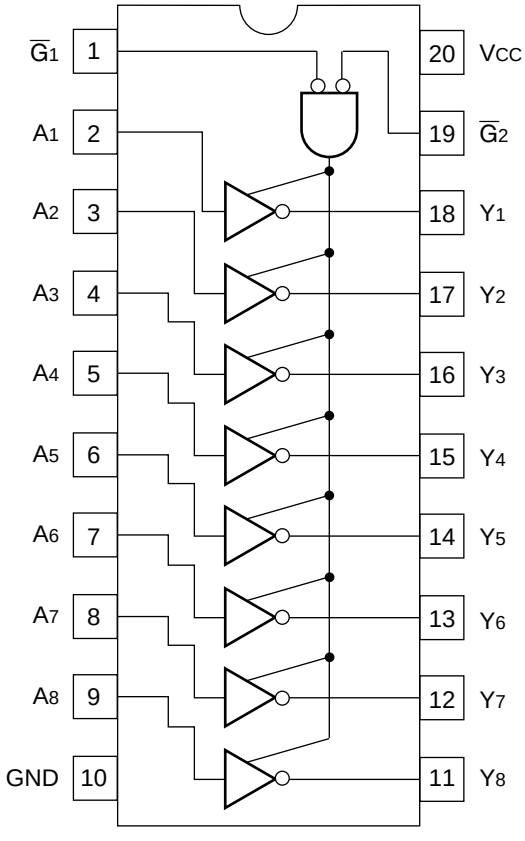
Inputs			Output Y	
$\overline{G_1}$	$\overline{G_2}$	A	HD74HC540	HD74HC541
L	L	L	H	L
L	L	H	L	H
H	X	X	Z	Z
X	H	X	Z	Z

X : irrelevant

Z : off (high-impedance) state of a 3-state output.

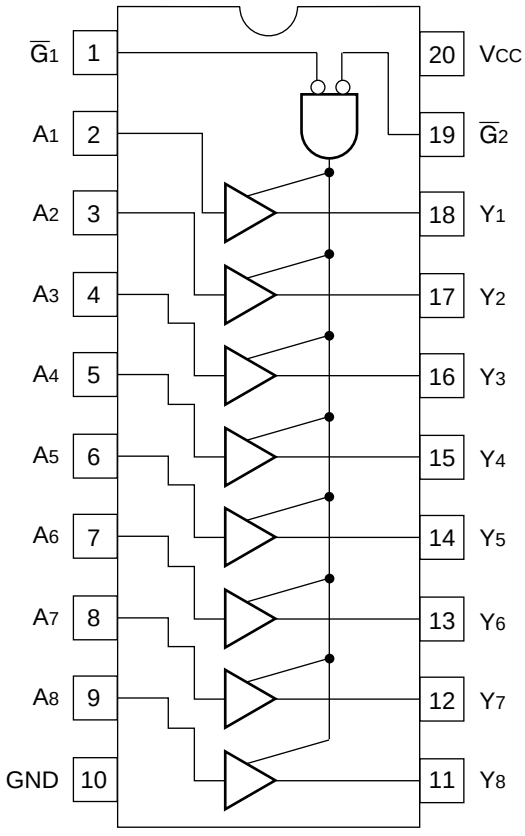
Pin Arrangement

HD74HC540



(Top view)

HD74HC541



(Top view)

Absolute Maximum Ratings

Item	Symbol	Rating	Unit
Supply voltage range	V_{CC}	–0.5 to +7.0	V
Input voltage	V_{IN}	–0.5 to V_{CC} + 0.5	V
Output voltage	V_{OUT}	–0.5 to V_{CC} + 0.5	V
Output current	I_{OUT}	±35	mA
DC current drai per V_{CC} GND	I_{CC}, I_{GND}	±75	mA
DC input diode current	I_{IK}	±20	mA
DC output diode current	I_{OK}	±20	mA
Power Dissipation per package	P_T	500	mW
Storage temperature	Tstg	–65 to +150	°C

DC Characteristics

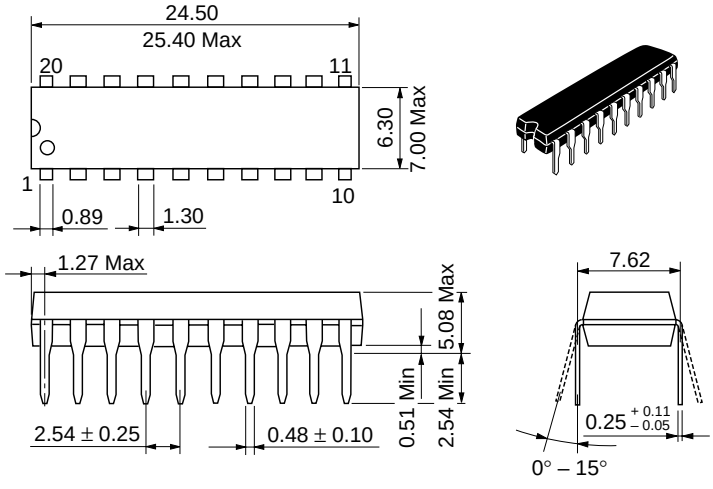
			Ta = 25°C			Ta = –40 to +85°C			
Item	**Symbol**	**V_{CC} (V)**	**Min**	**Typ**	**Max**	**Min**	**Max**	**Unit**	**Test Conditions**
Input voltage	V_{IH}	2.0	1.5	—	—	1.5	—	V	
		4.5	3.15	—	—	3.15	—		
		6.0	4.2	—	—	4.2	—		
	V_{IL}	2.0	—	—	0.3	—	0.3	V	
		4.5	—	—	1.35	—	1.35		
		6.0	—	—	1.8	—	1.8		
Hysteresis voltage	V_H	2.0	—	0.1	—	—	—	V	
		4.5	—	0.4	—	—	—		
		6.0	—	0.4	—	—	—		
Output voltage	V_{OH}	2.0	1.9	2.0	—	1.9	—	V	Vin = V_{IH} or V_{IL} I_{OH} = –20 µA
		4.5	4.4	4.5	—	4.4	—		
		6.0	5.9	6.0	—	5.9	—		
		4.5	4.18	—	—	4.13	—		I_{OH} = –6 mA
		6.0	5.68	—	—	5.63	—		I_{OH} = –7.8 mA
	V_{OL}	2.0	—	0.0	0.1	—	0.1	V	Vin = V_{IH} or V_{IL} I_{OL} = 20 µA
		4.5	—	0.0	0.1	—	0.1		
		6.0	—	0.0	0.1	—	0.1		
		4.5	—	—	0.26	—	0.33		I_{OL} = 6 mA
		6.0	—	—	0.26	—	0.33		I_{OL} = 7.8 mA
Off-state output current	I_{OZ}	6.0	—	—	±0.5	—	±5.0	µA	Vin = V_{IH} or V_{IL}, Vout = V_{CC} or GND
Input current	Iin	6.0	—	—	±0.1	—	±1.0	µA	Vin = V_{CC} or GND
Quiescent supply current	I_{CC}	6.0	—	—	4.0	—	40	µA	Vin = V_{CC} or GND, Iout = 0 µA

AC Characteristics (C_L = 50 pF, Input t_r = t_f = 6 ns)

			Ta = 25°C			Ta = –40 to +85°C			
Item	**Symbol**	**V_{cc} (V)**	**Min**	**Typ**	**Max**	**Min**	**Max**	**Unit**	**Test Conditions**
Propagation delay time	t_{PLH}	2.0	—	—	100	—	125	ns	(HD74HC540 only)
	t_{PHL}	4.5	—	11	20	—	25		
		6.0	—	—	17	—	21		
	t_{PLH}	2.0	—	—	115	—	145	ns	(HD74HC541 only)
	t_{PHL}	4.5	—	12	23	—	29		
		6.0	—	—	20	—	25		
Output enable time	t_{ZH}	2.0	—	—	150	—	190	ns	
	t_{ZL}	4.5	—	14	30	—	38		
		6.0	—	—	26	—	33		
Output disable time	t_{HZ}	2.0	—	—	150	—	190	ns	
	t_{LZ}	4.5	—	16	30	—	38		
		6.0	—	—	26	—	33		
Output rise/fall time	t_{TLH}	2.0	—	—	60	—	75	ns	
	t_{THL}	4.5	—	4	12	—	15		
		6.0	—	—	10	—	13		
Input capacitance	Cin	—	—	5	10	—	10	pF	

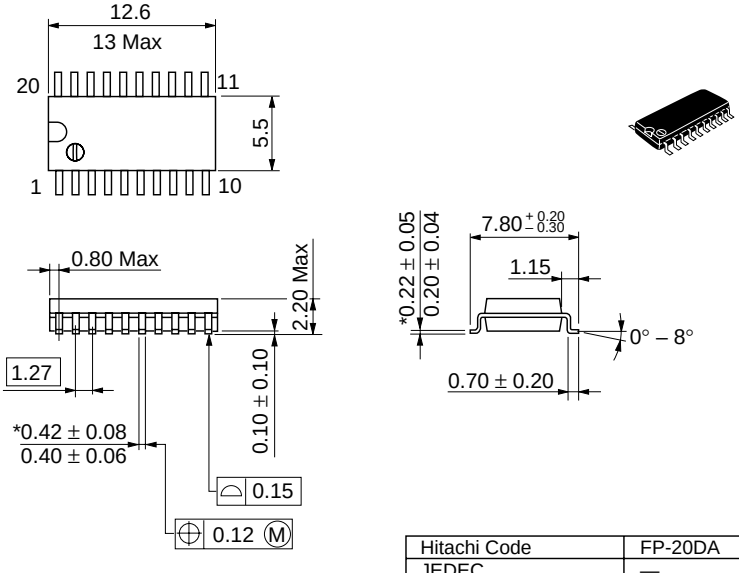
Package Dimensions

Unit: mm



Hitachi Code	DP-20N
JEDEC	—
EIAJ	Conforms
Mass (reference value)	1.26 g

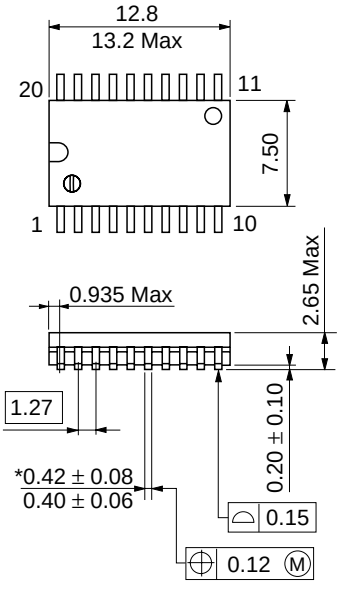
Unit: mm

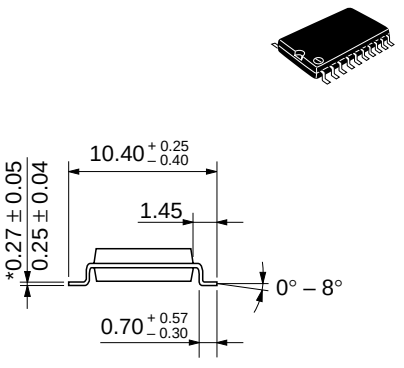


*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-20DA
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.31 g

Unit: mm

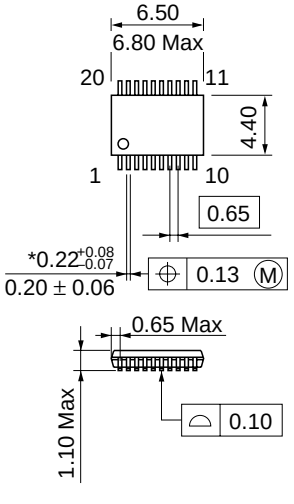


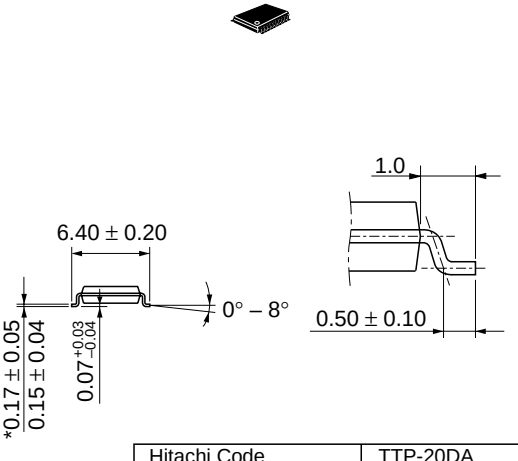


*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-20DB
JEDEC	Conforms
EIAJ	—
Mass (reference value)	0.52 g

Unit: mm





*Dimension including the plating thickness
Base material dimension

Hitachi Code	TTP-20DA
JEDEC	—
EIAJ	—
Mass (reference value)	0.07 g

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